

IN THE SPECIFICATION

Please replace the paragraph at page 7, lines 10-14, with the following rewritten paragraph:

As shown in Figs. 1 to 4, the semiconductor device 1 according to the first embodiment comprises a semiconductor integrated circuit 10 having a plurality of functional blocks, a package 2 for storing the semiconductor integrated circuit 10 therein, and a ground terminal 16, the plurality of signal terminals 4 and the single power supply terminal 8 which are exposed to the outside of the package 2.

Please replace the paragraph at page 9, lines 12-18, with the following rewritten paragraph:

A clock signal on which the operation of the digital circuit is based or some other input signal, for example, is applied from the outside of the semiconductor device 1 to one of the signal terminals 4 which is connected to the functional block 11. As a result, the external input signal is provided to the functional block 11. An output signal from the functional block 11 is provided to another of the signal terminals 4 which is connected to the functional block 11. This allows a device external to the semiconductor device 1 to receive the output signal from the functional block 11.

Please replace the paragraph at page 9, line 19, to page 10, line 2, with the following rewritten paragraph:

A high-frequency signal, for example, received by an antenna (not shown) is applied from the outside of the semiconductor device 1 to one of the signal terminals 4 which is connected to the functional block 12. As a result, the high-frequency signal is provided to the functional block 12. An output signal from the functional block 12 is applied to another of

the signal terminals 4 which is connected to the functional block 12. The signal terminals 4 which receive signals from the outside of the semiconductor device 1 are also referred to hereinafter as “input signal terminals 4,” and the signal terminals 4 which receive output signals from the functional blocks ~~11 and 12~~ 11 and 12 are also referred to hereinafter as “output signal terminals 4.”

Please replace the paragraph at page 10, lines 10-16, with the following rewritten paragraph:

Power, e.g. a positive potential, required to operate the semiconductor integrated circuit 10 is applied from the outside of the semiconductor device 1 to the power supply terminal 8. This provides power to the functional blocks 11 and 12 through the power supply terminal ~~[[7]]~~ 8. Thus, the functional block 11 operates on the basis of the ground potential applied thereto through the ground terminal 5, and the functional block 12 operates on the basis of the ground potential applied thereto through the ground terminal 6.

Please replace the paragraph at page 13, lines 13-20, with the following rewritten paragraph:

As shown in Figs. 6 and 7, the ground terminals 35 and 36 are bonded by aluminum wires 43 to the electrodes 25 and 26, respectively, of the semiconductor chip 21 within the package ~~[[2]]~~ 32. This provides an electrical connection between the ground terminal 35 and the functional block 11, and an electrical connection between the ground terminal 36 and the functional block 12. The size of the insulating substrate 42 smaller than that of the ground terminal 35 allows the connection through the aluminum wires 43 between the electrode 26 formed on the upper surface of the semiconductor chip 21 and the ground terminal 35.

Please replace the paragraph at page 14, lines 12-16, with the following rewritten paragraph:

The second embodiment, in which one of the ground terminals surrounds the other ground terminal, can reduce the variations in potential at the other ground terminal at least due to the potential change at the signal terminals 4. Consequently, the semiconductor device [[32]] 31 achieves higher performance than the semiconductor device 1 of the first embodiment.

Please cancel the Abstract at page 20, lines 1-13, in its entirety and replace with the following new Abstract:

ABSTRACT

A semiconductor device having a ground terminal and a plurality of signal terminals arranged around the ground terminal. The device features isolation between a first ground terminal connected to a first functional block and a second ground terminal connected to a second functional block. Thus, a ground potential applied to one of the functional blocks through the corresponding ground terminal is prevented from varying depending on the magnitude of a current flowing through the other functional block. This improves the performance of each functional block to improve the performance of the semiconductor device.